

isc N-Channel MOSFET Transistor

TK16G60W

• FEATURES

- Low drain-source on-resistance: R_{DS}(on) ≤0.19Ω.
- Enhancement mode:
 Vth =2.7 to 3.7V (VDS = 10 V, ID=0.79mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

· Switching Voltage Regulators

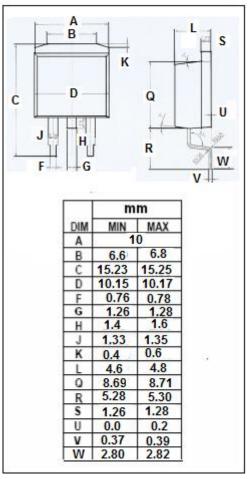
pin 1.Gate 2.Drain 3.Source TO-263 package

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V _G s	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous	15.8	Α
I _{DM}	Drain Current-Single Pulsed	63.2	Α
P _D	Total Dissipation @T _C =25℃	130	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.962	°C/W



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =10mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10V; I _D =0.79mA	2.7		3.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =7.9A			0.19	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V			10	μ А
V_{SDF}	Diode forward voltage	I _{DR} =15.8A, V _{GS} = 0 V			1.7	V

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